



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

13A

Features

- RDS(ON), VGS@10V, ID@6.5A<115mΩ
- RDS(ON) , VGS@4.5V, ID@4A<120mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

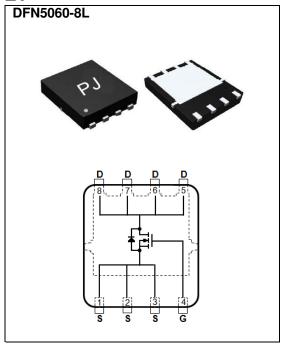
Mechanical Data

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0028 ounces, 0.08 grams

Marking: Q5472A



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Dusin Comment	T _C =25°C		13	А	
Continuous Drain Current	T _C =100°C	l _D	8		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	52		
Power Dissipation	T _C =25°C	Po	41	W	
	T _C =100°C		16		
Continuous Drain Current	T _A =25°C	I _D	2.9	Α	
	T _A =70°C		2.3	Α	
Power Dissipation	T _A =25°C	Po	2.0	\A/	
	T _A =70°C		1.3	W	
Single Pulse Avalanche Energy (Note 6)		E _{AS}	6.1	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
T : 17	Junction to Case	$R_{ heta JC}$	3.05	°C/W	
Typical Thermal Resistance (Note 4,5)	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V,I_D=250uA$	100	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.76	2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = 10V, I_D = 6.5A$	-	92	115	mΩ	
		V_{GS} =4.5 V , I_D =4 A	-	95	120		
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1.0	uA	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_g	V _{DS} =50V, I _D =2A, V _{GS} =10V ^(Note 1,2)	-	20	-	nC	
Gate-Source Charge	Q_{gs}		-	3.2	-		
Gate-Drain Charge	Q_gd		-	3.6	-		
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	1413	-	pF	
Output Capacitance	Coss		-	60	-		
Reverse Transfer Capacitance	Crss		-	34	-		
Turn-On Delay Time	td _(on)	V_{DD} =50V, I_{D} =1A, V_{GS} =10V, R_{G} =3.3 Ω (Note 1,2)	-	18	-	ns	
Turn-On Rise Time	t _r		-	4.3	-		
Turn-Off Delay Time	td _(off)		-	41	-		
Turn-Off Fall Time	t _f	n _G =3.312	-	4.2	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	13	Α	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.73	1	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =11A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

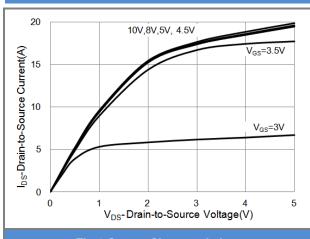


Fig.1 Output Characteristics

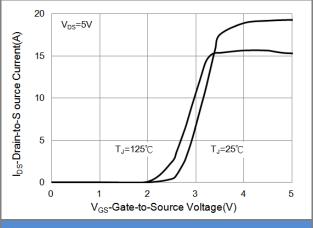


Fig.2 Transfer Characteristics

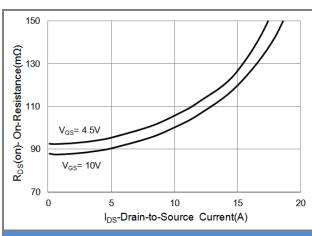


Fig.3 On-Resistance vs. Drain Current

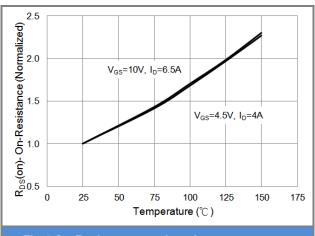


Fig.4 On-Resistance vs. Junction temperature

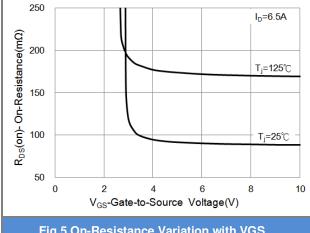


Fig.5 On-Resistance Variation with VGS.

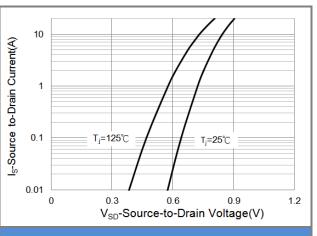


Fig.6 Source-Drain Diode Forward Voltage





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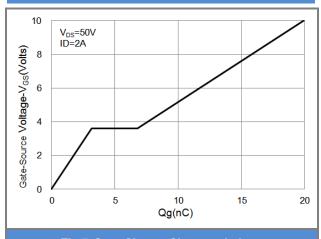


Fig.7 Gate-Charge Characteristics

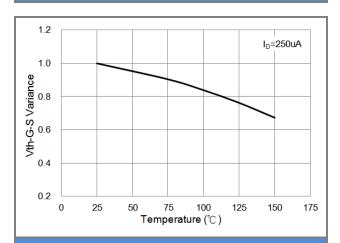
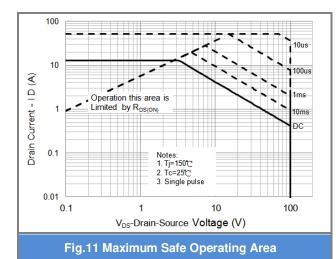


Fig.9 Threshold Voltage Variation with Temperature



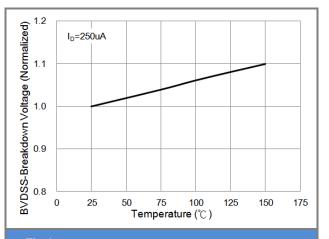


Fig.8 Breakdown Voltage Variation vs. Temperature

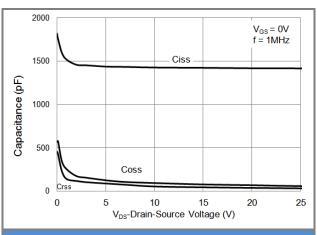


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

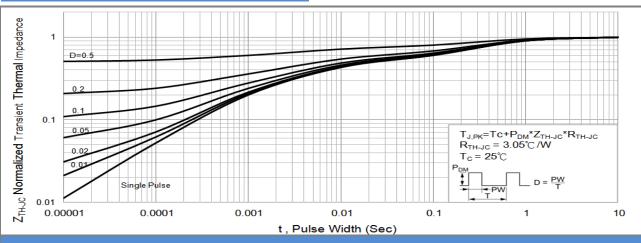


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

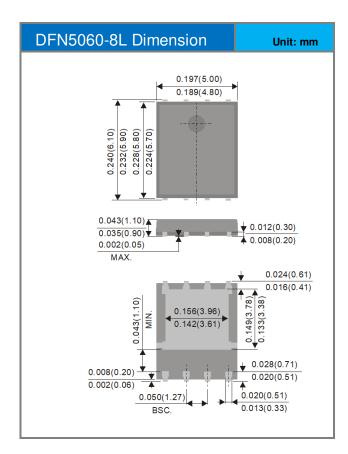


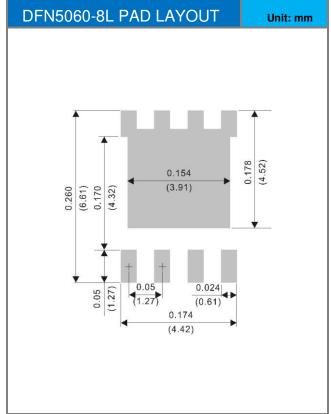


PART NO PACKING CODE VERSION

Part No Packing Code Package Type		Packing type	Marking	Version	
PJQ5472A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5472A	Halogen free	

Packaging Information & Mounting Pad Layout









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